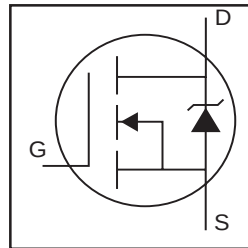


HEXFET® Power MOSFET Die in Wafer Form



60 V  
Size 4.0  
Rds(on)=0.034Ω  
5" Wafer

### Electrical Characteristics ( Wafer Form )

| Parameter     | Description                          | Guaranteed (Min/Max) | Test Conditions                                     |
|---------------|--------------------------------------|----------------------|-----------------------------------------------------|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage    | 60V Min.             | $V_{GS} = 0V$ , $I_D = 100\mu A$                    |
| $R_{DS(on)}$  | Static Drain-to-Source On-Resistance | 0.034Ω Max.          | $V_{GS} = 10V$ , $I_D = 5.0A$                       |
| $V_{GS(th)}$  | Gate Threshold Voltage               | 2.1V Min.            | $V_{DS} = 5.0V$ , $I_D = 250\mu A$                  |
| $I_{DSS}$     | Drain-to-Source Leakage Current      | 100μA Max.           | $V_{DS} = 60V$ , $V_{GS} = 0V$ , $T_J = 25^\circ C$ |
| $I_{GSS}$     | Gate-to-Source Leakage               | ± 10μA Max.          | $V_{GS} = \pm 20V$                                  |
| $T_J$         | Operating Junction and               | 125°C Max.           |                                                     |
| $T_{STG}$     | Storage Temperature Range            |                      |                                                     |

### Mechanical Data

|                                             |                                                                               |
|---------------------------------------------|-------------------------------------------------------------------------------|
| Nominal Backmetal Composition, Thickness:   | Cr-NiV-Ag ( 1kA°-2kA°-2.5kA° )                                                |
| Nominal Front Metal Composition, Thickness: | 99% Al, 1% Si (0.004mm)                                                       |
| Dimensions:                                 | 0.170" x 0.180" ( 4.32mm x 4.57 mm)                                           |
| Wafer Diameter:                             | 125mm with 100 flat                                                           |
| Wafer thickness:                            | 0.375mm + / -0.020mm                                                          |
| Relevant Die Mechanical Dwg. Number         | 01-5018                                                                       |
| Minimum Street Width                        | 0.084 mm                                                                      |
| Reject Ink Dot Size                         | 0.51mm Diameter Minimum                                                       |
| Recommended Storage Environment:            | Store in original container, in dessicated nitrogen, with no contamination    |
| Recommended Die Attach Conditions           | For optimum electrical results, die attach temperature should not exceed 300C |

Reference Standard IR packaged part ( for design ) : IRFZ44

### Die Outline

